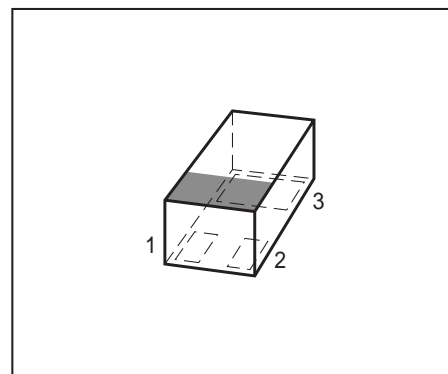


**NPN Silicon RF Transistor\***

- For low noise, high-gain broadband amplifiers at collector currents from 1 mA to 20 mA
- $f_T = 9$  GHz,  $F = 1$  dB at 1 GHz
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101

\* Short term description



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration			Package
BFR949L3	RK	1 = B	2 = E	3 = C	TSLP-3-1

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	10	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	1.5	
Collector current	$I_C$	50	mA
Base current	$I_B$	5	
Total power dissipation <sup>2)</sup> $T_S \leq 101$ °C	$P_{tot}$	250	mW
Junction temperature	$T_j$	150	°C
Ambient temperature	$T_A$	-65 ... 150	
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>3)</sup>	$R_{thJS}$	$\leq 195$	K/W

<sup>1)</sup>Pb-containing package may be available upon special request

<sup>2)</sup> $T_S$  is measured on the collector lead at the soldering point to the pcb

<sup>3)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

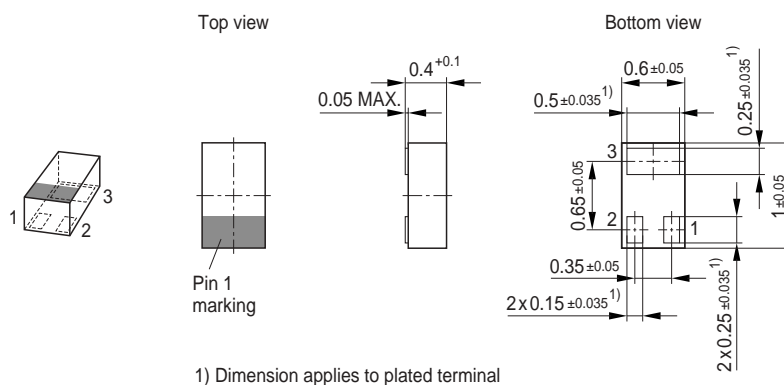
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$ , $I_B = 0$	$V_{(BR)CEO}$	10	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}$ , $V_{BE} = 0$	$I_{CES}$	-	-	100	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10\text{ V}$ , $I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}$ , $I_C = 0$	$I_{EBO}$	-	-	0.1	$\mu\text{A}$
DC current gain- $I_C = 5\text{ mA}$ , $V_{CE} = 6\text{ V}$ , pulse measured	$h_{FE}$	100	140	180	-

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 15\text{ mA}$ , $V_{CE} = 6\text{ V}$ , $f = 1\text{ GHz}$	$f_T$	7	9	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , emitter grounded	$C_{cb}$	-	0.25	0.4	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , base grounded	$C_{ce}$	-	0.15	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$ , $V_{CB} = 0$ , collector grounded	$C_{eb}$	-	0.7	-	
Noise figure $I_C = 5\text{ mA}$ , $V_{CE} = 6\text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 1\text{ GHz}$ $I_C = 3\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 1.8\text{ GHz}$	$F$	-  -	1  1.3	2.5  -	dB
Power gain <sup>1)</sup> $I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 900\text{ MHz}$	$G_{ms}$	-	21.5	-	-
Power gain, maximum available <sup>1)</sup> $I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 1.8\text{ GHz}$	$G_{ma}$	-	15.5	-	dB
Transducer gain $I_C = 15\text{ mA}$ , $V_{CE} = 6\text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 1\text{ GHz}$ $I_C = 10\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	14  -	17  12	-  -	dB

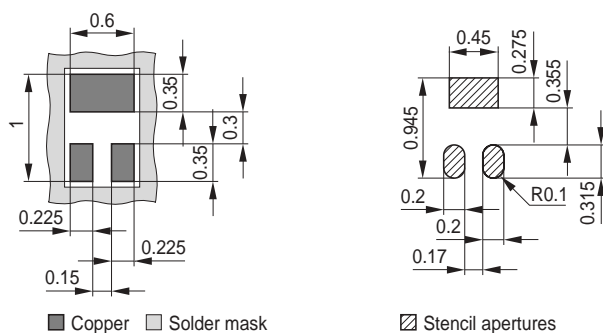
<sup>1)</sup>  $G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$ ,  $G_{ms} = |S_{21} / S_{12}|$

## Package Outline

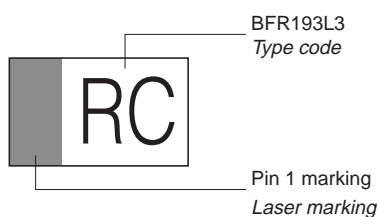


## Foot Print

For board assembly information please refer to Infineon website "Packages"

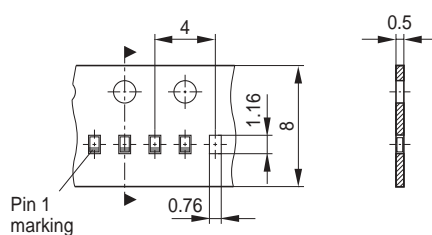


## Marking Layout (Example)



## Standard Packing

Reel  $\varnothing$ 180 mm = 15.000 Pieces/Reel



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